

EO-532-G/0.2~0.4mJ

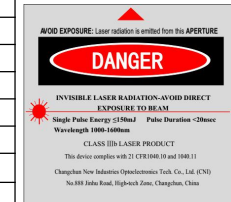
**HIGH ENERGY DIODE
PUMPED ALL-SOLID-STATE
Q-SWITCHED LASER**

High energy diode pumped all solid state Q-switched laser at 532nm has the features of high single pulse energy, short pulse duration, and high peak power, which is widely used in radar, topography measurement, marking, ranging, glass carving, micro-processing, scientific research, and so on.



SPECIFICATIONS

Wavelength (nm)	532±1		
Operating mode	Q-switched: EO (Electro-optic)		
Single pulse energy (mJ)	0.4@1KHz	0.4@5KHz	0.06@25KHz
Pulse duration (ns)	<8@1KHz	<8@5KHz	<15@25KHz
Rep. rate (kHz)	1Hz~1kHz	1k~7kHz	1k~25kHz
Power stability (rms)	<1%, <2%		
M ²	<1.2		
Pointing stability (urad, std)	<20		
Beam divergence, full angle (mrad)	<3		
Beam diameter (mm)	~1		
Beam height from base plate (mm)	80		
Warm-up time (minutes)	<15		
Cooled method	Air cooled		
Operating temperature (°C)	15~30		
Power supply (DC 24V)	PSU-EO-G		
Expected lifetime (hours)	10000		
Warranty period	1 year		
Options	Higher energy can be customized; Higher frequency can be customized		



EO-532-G	PSU-EO-G(DC 24V)
<p>242(L)×210(W)×112.5(H)mm³ 5.8kg</p>	<p>366(L)×264(W)×102(H)mm³ 6.5kg</p>